The listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

- 1.-3. (Canceled)
- 4. (Currently Amended) A semiconductor device comprising:
- a substrate;
- an adhesive material over the substrate;
- a protective film over the adhesive material, said protective film comprising Teflon;
  - an insulating film over the protective film; and
- a middle processing component comprising a control section and an operation section, and a memory unit a thin film transistor over the insulating film,
- wherein the middle processing component includes a thin film transistor of nchannel type and a thin film transistor of p-channel type.
- 5. (Previously Presented) A semiconductor device according to claim 4, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.
  - 6.-19. (Canceled)
  - 20. (Previously Presented) A semiconductor device comprising:
  - a substrate;
  - an adhesive material over the substrate; and

a protective film over the adhesive material;

an insulating film over the protective film;

a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film; and

a battery over the substrate;

wherein the middle processing component includes a thin film transistor of nchannel type and a thin film transistor of p-channel type.

## 21.-27. (Canceled)

28. (Previously Presented) A semiconductor device comprising:

a plastic substrate;

an adhesive material over the plastic substrate; and

a protective film over the adhesive material, said protective film comprising a material selected from the group consisting of SnO<sub>2</sub>, SrO, Teflon, and metal;

an insulating film over the protective film, said insulating film comprising silicon oxynitride;

a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film; and

a battery over the plastic substrate;

wherein the middle processing component includes a thin film transistor of nchannel type and a thin film transistor of p-channel type.

29. (Previously Presented) A semiconductor device comprising:

a plastic substrate;

an adhesive material over the plastic substrate; and

a protective film over the adhesive material, said protective film comprising a material selected from the group consisting of SnO<sub>2</sub>, SrO, Teflon, and metal;

an insulating film over the protective film;

a middle processing component comprising a control section and an operation section, and a memory unit over the insulating film; and

wherein the middle processing component includes a thin film transistor of nchannel type and a thin film transistor of p-channel type.

- 30. (Previously Presented) A semiconductor device according to claim 28, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.
- 31. (Previously Presented) A semiconductor device according to claim 29, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.